International
IOR Rectifier

IR2153Z

SELF-OSCILLATING HALF-BRIDGE DRIVER

Features

- Floating channel designed for bootstrap operation
  Fully operational to +600V
  Tolerant to negative transient voltage
  dV/dt immune
- Undervoltage lockout
- Programmable oscillator frequency

$$f = \frac{1}{1.4 \times (R_T + 75\Omega) \times C_T}$$

- Matched propagation delay for both channels
- Micropower supply startup current of 90 µA.
- Shutdown function turns off both channels
- Low side output in phase with R_T

Product Summary

V_{OFFSET}	600V max.
Duty Cycle	50%
I_O+/-	200 mA / 400 mA
V_{clamp}	15.6V
Deadtime (typ.)	1.2 µs

Description

The IR2153Z is a high voltage, high speed, self-oscillating power MOSFET and IGBT driver with both high and low side referenced output channels. Proprietary HVIC and latch immune CMOS technologies enable ruggedized monolithic construction. The front end features a programmable oscillator which is similar to the 555 timer. The output drivers feature a high pulse current buffer stage and an internal deadtime designed for minimum driver cross-conduction. Propagation delays for the two channels are matched to simplify use in 50% duty cycle applications. The floating channel can be used to drive an N-channel power MOSFET or IGBT in the high side configuration that operates off a high voltage rail up to 600 volts.

Absolute Maximum Ratings

Absolute Maximum Ratings indicate sustained limits beyond which damage to the device may occur. All voltage parameters are absolute voltages referenced to COM. The Thermal Resistance and Power Dissipation ratings are measured under board mounted and still air conditions.

Symbol	Parameter	Min.	Max.	Units
V_B	High Side Floating Supply Voltage	-0.3	625	
V_S	High Side Floating Supply Offset Voltage	V_B - 25	V_B + 0.3	
V_{HO}	High Side Floating Output Voltage	V_S - 0.3	V_B + 0.3	V
V_{LO}	Low Side Output Voltage	-0.3	V_{CC} + 0.3	
V_{RT}	R_T Voltage	-0.3	V_{CC} + 0.3	
V_{CT}	C_T Voltage	-0.3	V_{CC} + 0.3	
I_{CC}	Supply Current (Note 1)	—	25	
I_{RT}	R_T Output Current	-5	5	mA
dV_S/dt	Allowable Offset Supply Voltage Transient	—	50	V/ns
P_D	Package Power Dissipation @ T_A £ +25°C	—	1.0	W
Rth_{JA}	Thermal Resistance, Junction to Ambient	—	100	°C/W
T_J	Junction Temperature	-55	125	
T_S	Storage Temperature	-55	150	°C
T_L	Lead Temperature (Soldering, 10 seconds)	—	300	

Recommended Operating Conditions

The Input/Output logic timing diagram is shown in Figure 1. For proper operation the device should be used within the recommended conditions. The V_S offset rating is tested with all supplies biased at 15V differential.

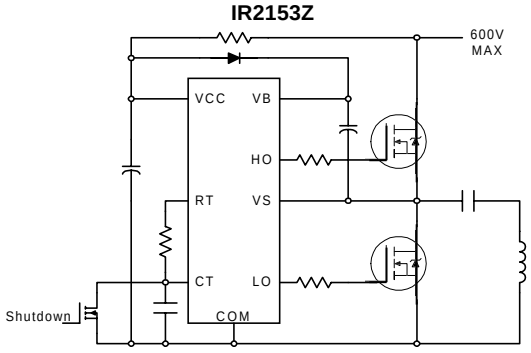
Symbol	Definition	Min.	Max.	Units
V_B	High Side Floating Supply Absolute Voltage	V_S + 10	V_S + 20	V
V_S	High Side Floating Supply Offset Voltage	—	600	
V_{HO}	High Side Floating Output Voltage	V_S	V_B	
V_{LO}	Low Side Output Voltage	0	V_{CC}	
I_{CC}	Supply Current (Note 1)	—	5	mA

Dynamic Electrical Characteristics

V_{BIAS} (V_{CC}, V_{BS}) = 12V, C_L = 1000 pF and T_A = 25°C unless otherwise specified.

Symbol	Definition	Min.	Typ.	Max.	Units	Test Conditions
t_r	Turn-On Rise Time	—	80	165	ns	
t_f	Turn-Off Fall Time	—	35	100		
t_{sd}	Shutdown Propagation Delay	—	660	—		
DT	Deadtime	—	1.2	—	µs	
D	R_T Duty Cycle	—	50	—	%	

Typical Connections



Note 1: Because of the IR2153's application specificity toward off-line supply systems, this IC contains a zener clamp structure between the chip V_{CC} and COM which has a nominal breakdown voltage of 15.6V. Therefore, the IC supply voltage is normally derived by forcing current into the supply lead (typically by means of a high value resistor connected between the chip V_{CC} and the rectified line voltage and a local decoupling capacitor from V_{CC} to COM) and allowing the internal zener clamp circuit to determine the nominal supply voltage. Therefore, this circuit should not be driven by a DC, low impedance power source of greater than V_{CLAMP}.

Static Electrical Characteristics

V_{BIAS} (V_{CC}, V_{BS}) = 12V, C_L = 1000 pF, C_T = 1 nF and T_A = 25°C unless otherwise specified. The V_{IN}, V_{TH} and I_{IN} parameters are referenced to COM. The V_O and I_O parameters are referenced to COM and are applicable to the respective output leads: HO or LO.

Symbol	Definition	Min.	Typ.	Max.	Units	Test Conditions
f_{OSC}	Oscillator Frequency	—	20.0	—	kHz	R_T = 35.7 kW
		—	100	—		R_T = 7.04 kW
V_{CLAMP}	V_{CC} Zener Shunt Clamp Voltage	—	15.6	—	V	I_{CC} = 5 mA
V_{CT+}	2/3 V_{CC} Threshold	—	8.0	—		
V_{CT-}	1/3 V_{CC} Threshold	—	4.0	—		
V_{CTSD}	C_T shutdown Input Threshold	—	2.2	—		
V_{RT+}	R_T High Level Output Voltage, V_{CC} - R_T	—	0	100	mV	I_{RT} = -100 µA
		—	200	300		I_{RT} = -1 mA
V_{RT-}	R_T Low Level Output Voltage	—	20	50		I_{RT} = 100 µA
		—	200	300		I_{RT} = 1 mA
V_{OH}	High Level Output Voltage, V_{BIAS} - V_O	—	—	100		I_O = 0A
V_{OL}	Low Level Output Voltage, V_O	—	—	100		I_O = 0A
I_{LK}	Offset Supply Leakage Current	—	—	50	µA	V_B = V_S = 600V
I_{QBS}	Quiescent V_{BS} Supply Current	—	10	—		
I_{QCCUV}	Micropower V_{CC} Supply Startup Current	—	90	—		V_{CC} < V_{CCUV}
I_{QCC}	Quiescent V_{CC} Supply Current	—	400	—		V_{CC} > V_{CCUV}
I_{CT}	C_T Input Current	—	0.001	1.0		
V_{CCUV+}	V_{CC} Supply Undervoltage Positive Going Threshold	—	9.0	—	V	
V_{CCUV-}	V_{CC} Supply Undervoltage Negative Going Threshold	—	8.0	—		
V_{CCUVH}	V_{CC} Supply Undervoltage Lockout Hysteresis	—	1.0	—	V	
I_{O+}	Output High Short Circuit Pulsed Current	—	200	—	mA	V_O = 0V
I_{O-}	Output Low Short Circuit Pulsed Current	—	400	—		V_O = 15V

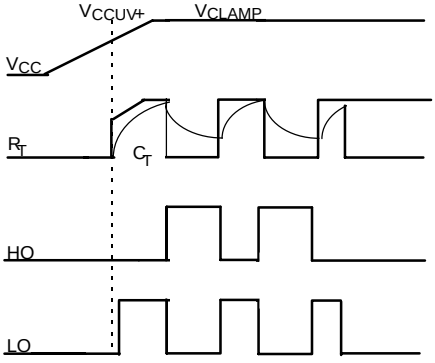


Figure 1. Input/Output Timing Diagram

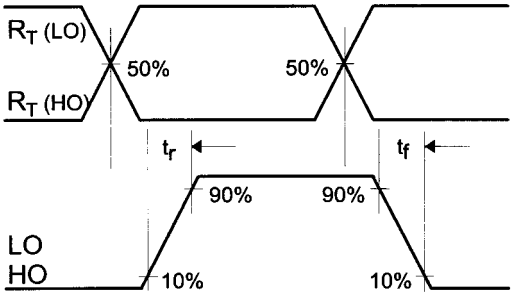


Figure 2. Switching Time Waveform Definitions

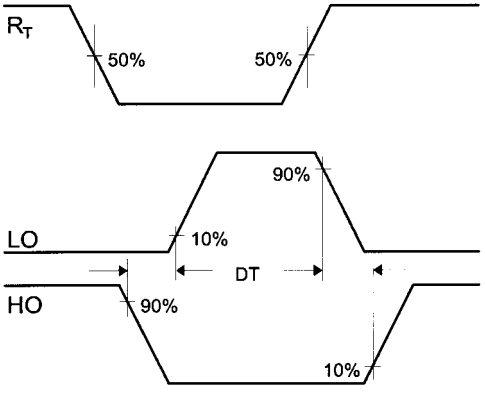
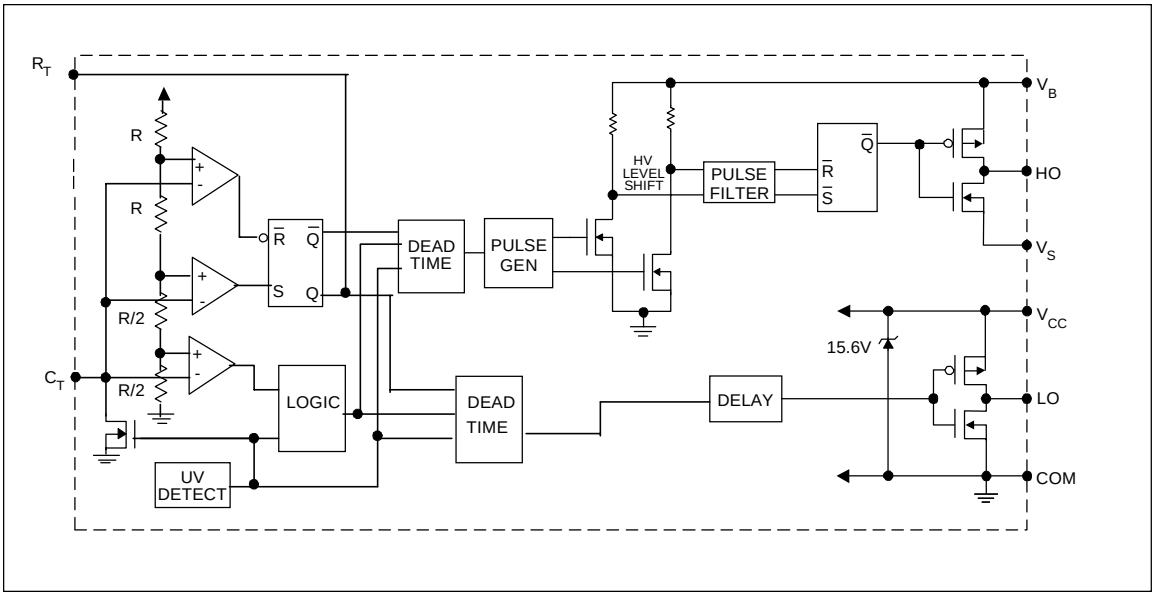


Figure 3. Deadtime Waveform Definitions

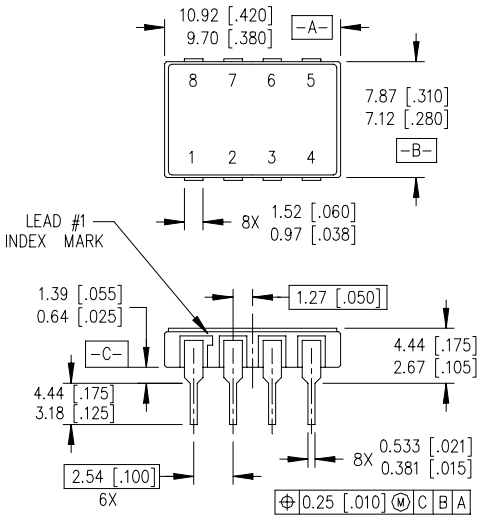
Functional Block Diagram

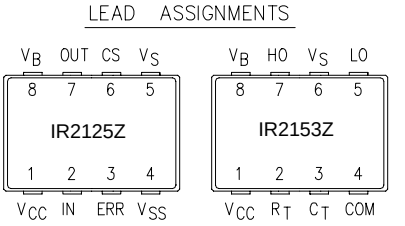


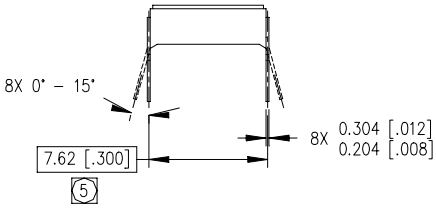
Lead Definitions

Lead Symbol	Description
R_T	Oscillator timing resistor input,in phase with HO for normal IC operation
C_T	Oscillator timing capacitor input, the oscillator frequency according to the following equation: $f = \frac{1}{1.4 \times (R_T + 75\Omega) \times C_T}$ where 75W is the effective impedance of the R_T output stage
V_B	High side floating supply
HO	High side gate drive output
V_S	High side floating supply return
V_{CC}	Low side and logic fixed supply
LO	Low side gate drive output
COM	Low side return

Case Outline and Dimensions MO-036AA







NOTES:

1. DIMENSIONING & TOLERANCING PER ANSI Y14.5M–1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
4. OUTLINE CONFORMS TO JEDEC OUTLINE MO–036AA.
5. MEASURED WITH THE LEADS CONSTRAINED TO BE PERPENDICULAR TO DATUM PLANE C.

International
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WORLD HEADQUARTERS: 233 Kansas St., El Segundo, California 90245, Tel: (310) 322 3331
IR GREAT BRITAIN: Hurst Green, Oxted, Surrey RH8 9BB, UK Tel: ++ 44 1883 732020
IR CANADA: 15 Lincoln Court, Brampton, Ontario L6T3Z2, Tel: (905) 453 2200
IR GERMANY: Saalburgstrasse 157, 61350 Bad Homburg Tel: ++ 49 6172 96590
IR ITALY: Via Liguria 49, 10071 Borgaro, Torino Tel: ++ 39 11 451 0111
IR FAR EAST: K&H Bldg., 2F, 30-4 Nishi-Ikebukuro 3-Chome, Toshima-Ku, Tokyo Japan 171 Tel: 81 3 3983 0086
IR SOUTHEAST ASIA: 1 Kim Seng Promenade, Great World City West Tower, 13-11, Singapore 237994 Tel: ++ 65 221 8371
IR TAIWAN:16 Fl. Suite D. 207, Sec. 2, Tun Haw South Road, Taipei, 10673, Taiwan Tel: 886-2-2377-9936
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